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Probleme de fiabilitate ale diodelor cu siliciu realizate prin tehnologia bipolară

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Abstract
The main characteristics of the silicon diodes achieved by bipolar technology are described, followed by the typical failure mechanisms, which are identified and explained. In each case, corrective actions are suggested, aimed to reduce the failure risks and to improve the reliability of the electronic systems made by using these silicon diodes.

Keywords: silicon diodes, failure mechanism, corrective actions, reliability.

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